

DAP222M3T5G

Preferred Device

Product Preview

Common Anode Silicon Dual Switching Diodes

These Common Anode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. The DAP222 device is housed in the SOT-723 package which is designed for low power surface mount applications, where board space is at a premium.

- Fast t_{rr}
- Low C_D
- ESD Performance: Human Body Model; > 2000 V,
Machine Model > 200 V
- Available in 4 mm Tape and Reel
- This is a Pb-Free Device

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	80	V
Peak Reverse Voltage	V_{RM}	80	V
Forward Current	I_F	100	mA
Peak Forward Current	I_{FM}	300	mA
Peak Forward Surge Current	I_{FSM} (Note 1)	2.0	A

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation	P_D	260	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

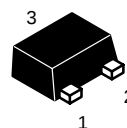
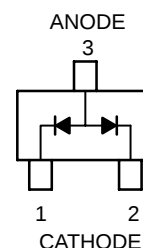
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. $t = 1.0 \mu\text{s}$.



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SOT-723
CASE 631AA
STYLE 4

MARKING DIAGRAM



P9 = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
DAP222M3T5G	SOT-723	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

DAP222M3T5G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I_R	$V_R = 70\text{ V}$	–	0.1	μA
Forward Voltage	V_F	$I_F = 100\text{ mA}$	–	1.2	V
Reverse Breakdown Voltage	V_R	$I_R = 100\text{ }\mu\text{A}$	80	–	V
Diode Capacitance	C_D	$V_R = 6.0\text{ V}$, $f = 1.0\text{ MHz}$	–	3.5	pF
Reverse Recovery Time	t_{rr} (Note 2)	$I_F = 5.0\text{ mA}$, $V_R = 6.0\text{ V}$, $R_L = 100\text{ }\Omega$, $I_{rr} = 0.1 I_R$	–	4.0	ns

2. t_{rr} Test Circuit for DAP222 in Figure 4.

TYPICAL ELECTRICAL CHARACTERISTICS

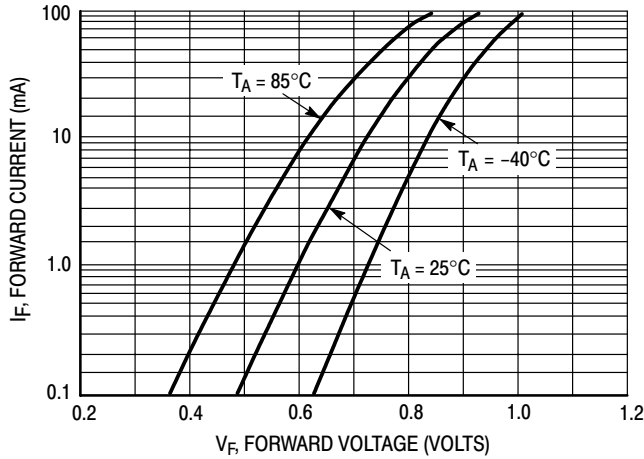


Figure 1. Forward Voltage

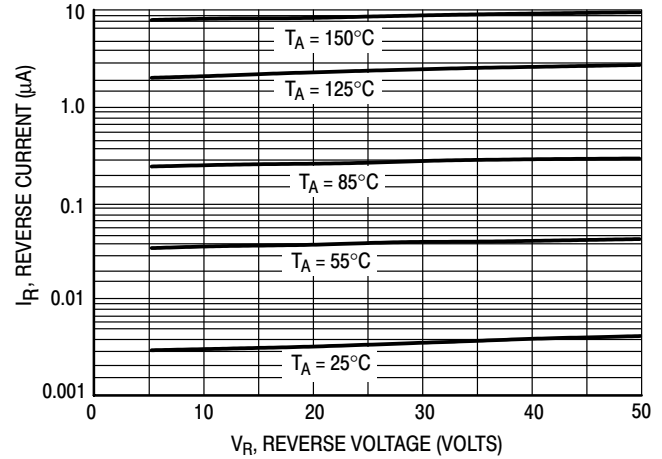


Figure 2. Reverse Current

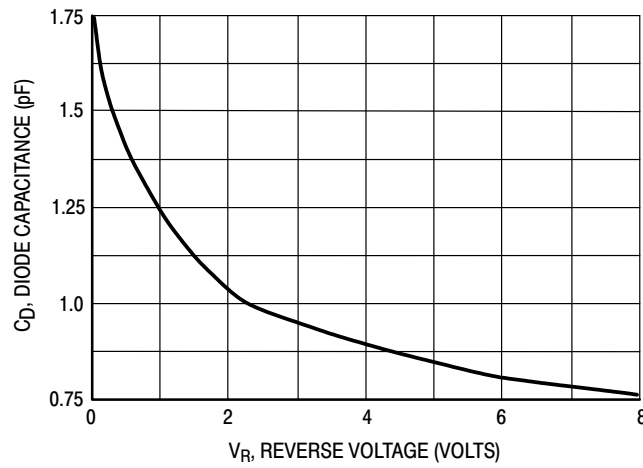
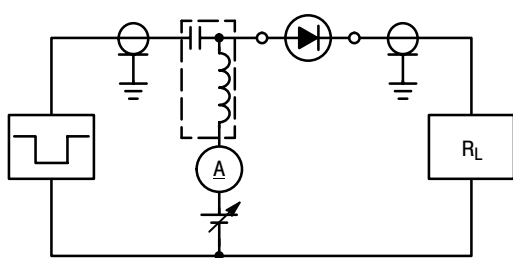
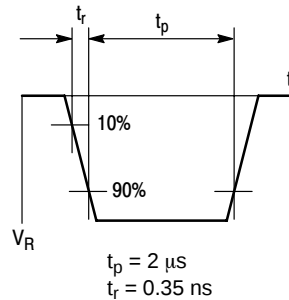


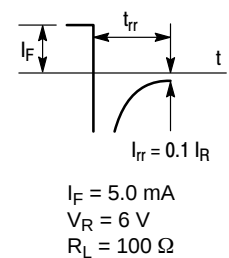
Figure 3. Diode Capacitance



RECOVERY TIME EQUIVALENT TEST CIRCUIT



INPUT PULSE



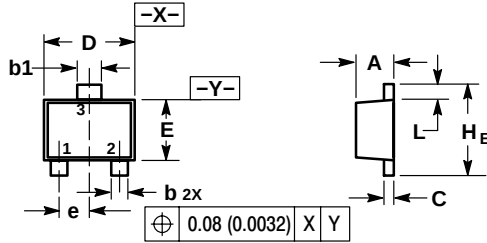
OUTPUT PULSE

Figure 4. Reverse Recovery Time Test Circuit

DAP222M3T5G

PACKAGE DIMENSIONS

SOT-723
CASE 631AA-01
ISSUE B



NOTES:

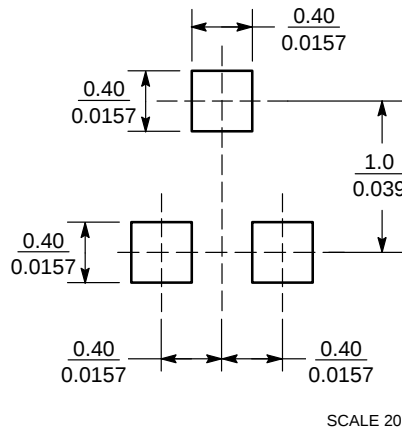
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.21	0.27	0.0059	0.0083	0.0106
b1	0.25	0.31	0.37	0.010	0.012	0.015
C	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.40 BSC			0.016 BSC		
H E	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

STYLE 4:

- PIN 1. CATHODE
- CATHODE
- ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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